Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-275-3065

	losure Material:
Ce	ramic
Οv	erall Length:
0.3	55 inches
Те	rminal Length:
0.1	75 inches
Οv	erall Height:
0.1	80 inches
Οv	erall Width:
0.2	70 inches
Мо	unting Method:
Те	rminal
Cri	ticality Code Justification:
Fea	at
Se	miconductor Material:
Ga	llium arsenide
Vo	Itage Rating In Volts Per Characteristic:
6.0	reverse voltage, dc
Cu	rrent Rating Per Characteristic:
60.	00 milliamperes source cutoff current preset
Po	wer Rating Per Characteristic:
30(	0.0 milliwatts small-signal input power, common-collector preset
Ма	ximum Operating Tempurature Per Measurement Point:
100	0.0 degrees celsius ambient air
•	ecial Features:
We	eapon system essential
Те	rminal Type And Quantity:
6 p	in
Sh	elf Life:
N/a	
Un	it Of Measure:
De	militarization:
No	
Fii	g: